

KM416S4020A

CMOS SDRAM

2M x 16Bit x 2 Banks Synchronous DRAM

FEATURES

- JEDEC standard 3.3V power supply
- LVTTTL compatible with multiplexed address
- Dual banks operation
- MRS cycle with address key programs
 - CAS Latency (2 & 3)
 - Burst Length (1, 2, 4, 8 & full page)
 - Burst Type (Sequential & Interleave)
- All inputs are sampled at the positive going edge of the system clock
- Burst Read Single-bit Write operation
- DQM for masking
- Auto & self refresh
- 64ms refresh period (4K cycle)

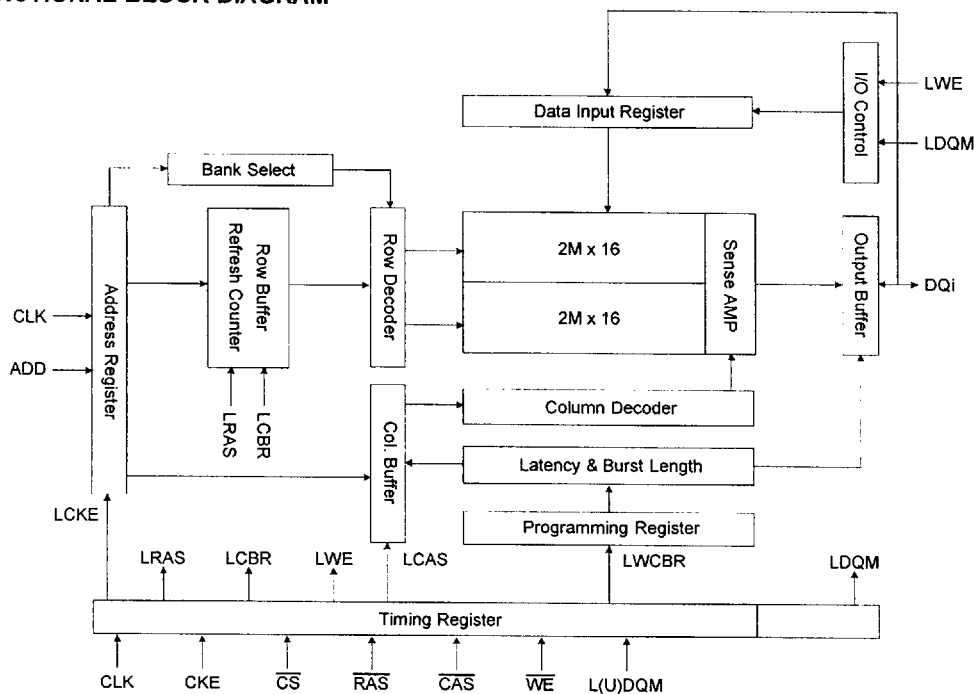
GENERAL DESCRIPTION

The KM416S4020A is 67,108,864 bits synchronous high data rate Dynamic RAM organized as 2 x 2,097,152 words by 16 bits, fabricated with SAMSUNG's high performance CMOS technology. Synchronous design allows precise cycle control with the use of system clock I/O transactions are possible on every clock cycle. Range of operating frequencies, programmable burst length and programmable latencies allow the same device to be useful for a variety of high bandwidth, high performance memory system applications.

ORDERING INFORMATION

Part NO.	MAX Freq.	Interface	Package
KM416S4020AT-G/F8	125MHz	LVTTTL	54 TSOP(II)
KM416S4020AT-G/F10	100MHz		
KM416S4020AT-G/F12	83MHz		

FUNCTIONAL BLOCK DIAGRAM



* Samsung Electronics reserves the right to change products or specification without notice.

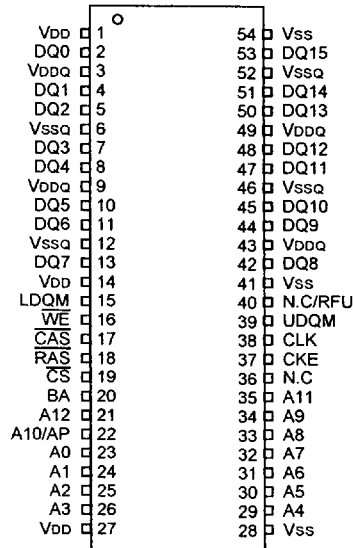


REV. 4 Mar. '97

KM416S4020A

CMOS SDRAM

PIN CONFIGURATION (TOP VIEW)



54PIN TSOP (II)
(400mil x 875mil)
(0.8 mm PIN PITCH)

PIN FUNCTION DESCRIPTION

PIN	NAME	INPUT FUNCTION
CLK	System Clock	Active on the positive going edge to sample all inputs.
\overline{CS}	Chip Select	Disables or enables device operation by masking or enabling all inputs except CLK, CKE and L(U)DQM
CKE	Clock Enable	Masks system clock to freeze operation from the next clock cycle. CKE should be enabled at least one cycle prior to new command. Disable input buffers for power down in standby.
A0 ~ A12	Address	Row / column addresses are multiplexed on the same pins. Row address : RA0 ~ RA12, column address : CA0 ~ CA7
BA	Bank Select Address	Selects bank to be activated during row address latch time. Selects bank for read/write during column address latch time.
\overline{RAS}	Row Address Strobe	Latches row addresses on the positive going edge of the CLK with \overline{RAS} low. Enables row access & precharge.
\overline{CAS}	Column Address Strobe	Latches column addresses on the positive going edge of the CLK with \overline{CAS} low. Enables column access.
\overline{WE}	Write Enable	Enables write operation and row precharge. Latches data in starting from \overline{CAS} , \overline{WE} active.
L(U)DQM	Data Input/Output Mask	Makes data output Hi-Z, tSHZ after the clock and masks the output. Blocks data input when L(U)DQM active.
DQ0 ~ 15	Data Input/Output	Data inputs/outputs are multiplexed on the same pins.
VDD/VSS	Power Supply/Ground	Power and ground for the input buffers and the core logic.
VDDQ/VSSQ	Data Output Power/Ground	Isolated power supply and ground for the output buffers to provide improved noise immunity.
N.C/RFU	No Connection/ Reserved for Future Use	This pin is recommended to be left No Connection on the device.



REV. 4 Mar. '97

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Voltage on any pin relative to Vss	V _{IN} , V _{OUT}	-1.0 ~ 4.6	V
Voltage on VDD supply relative to Vss	V _{DD} , V _{DDQ}	-1.0 ~ 4.6	V
Storage temperature	T _{STG}	-55 ~ +150	°C
Power dissipation	P _D	1	W
Short circuit current	I _{OS}	50	mA

Note : Permanent device damage may occur if ABSOLUTE MAXIMUM RATINGS are exceeded. Functional operation should be restricted to recommended operating condition. Exposure to higher than recommended voltage for extended periods of time could affect device reliability.

DC OPERATING CONDITIONS

Recommended operating conditions (Voltage referenced to Vss = 0V, TA = 0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit	Note
Supply voltage	V _{DD} , V _{DDQ}	3.0	3.3	3.6	V	
Input logic high voltage	V _{IH}	2.0	3.0	V _{DD} +0.3	V	1
Input logic low voltage	V _{IL}	-0.3	0	0.8	V	2
Output logic high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -2mA
Output logic low voltage	V _{OL}	-	-	0.4	V	I _{OL} = 2mA
Input leakage current	I _{IL}	-5	-	5	µA	3
Output leakage current	I _{OL}	-5	-	5	µA	4

Note : 1. V_{IH}(max) = 4.6V AC for pulse width ** 10ns acceptable.
 2. V_{IL}(min) = -1.5V AC for pulse width ** 10ns acceptable.
 3. Any input 0V ** V_{IN} ** V_{DD} + 0.3V, all other pins are not under test = 0V.
 4. Dout is disabled, 0V ** V_{OUT} ** V_{DD}.

CAPACITANCE (V_{DD} = 3.3V, TA = 25°C, f = 1MHz)

Parameter	Symbol	Min	Max	Unit
Input capacitance (A ₀ ~ A ₁₂ , BA)	C _{IN1}	2	4	pF
Input capacitance (CLK, CKE, CS, RAS, CAS, WE & L(U)DQM)	C _{IN2}	2	4	pF
Data input/output capacitance (DQ ₀ ~ DQ ₁₅)	C _{OUT}	2	5	pF



DC CHARACTERISTICS

(Recommended operating condition unless otherwise noted, TA = 0 to 70°C)

Parameter	Symbol	Test Condition	CAS Latency	Version			Unit	Note
				-8	-10	-12		
Operating Current (One Bank Active)	Icc1	Burst Length = 1 trc**trc(min) IoL = 0 mA		140	125	105	mA	1
Precharge Standby Current in power-down mode	Icc2P	CKE**VIL(max), tcc = 15ns		2			mA	
	Icc2PS	CKE & CLK**VIL(max), tcc = **		2				
Precharge Standby Current in non power-down mode	Icc2N	CKE**VIH(min), CS**VIH(min), tcc = 15ns Input signals are changed one time during 30ns		30			mA	
	Icc2NS	CKE**VIH(min), CLK**VIL(max), tcc = ** Input signals are stable		20				
Active Standby Current in power-down mode	Icc3P	CKE**VIL(max), tcc = 15ns		8			mA	
	Icc3PS	CKE & CLK**VIL(max), tcc = **		8				
Active Standby Current in non power-down mode (One Bank Active)	Icc3N	CKE**VIH(min), CS**VIH(min), tcc = 15ns Input signals are changed one time during 30ns		50			mA	
	Icc3NS	CKE**VIH(min), CLK**VIL(max), tcc = ** Input signals are stable		35				
Operating Current (Burst Mode)	Icc4	IoL = 0 mA Page Burst 2 Banks activated tccd = 2CLKs	3	200	165	135	mA	1
			2	140	130	115		
Refresh Current	Icc5	trc**trc(min)		210			mA	2
Self Refresh Current	Icc6	CKE**0.2V		3			mA	3
				500			uA	4

- Note :
1. Measured with outputs open.
 2. Refresh period is 64ms.
 3. KM416S4020AT-G**
 4. KM416S4020AT-F**

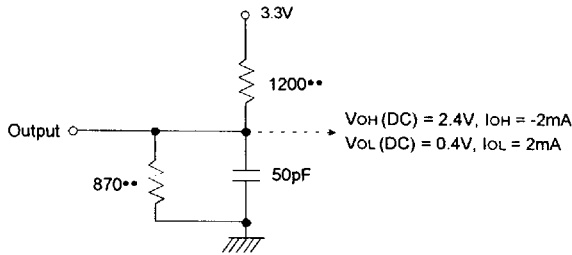


KM416S4020A

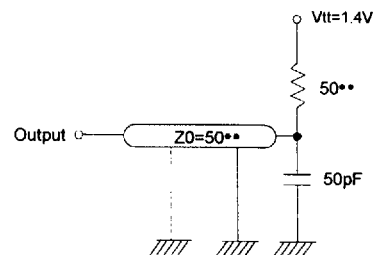
CMOS SDRAM

AC OPERATING TEST CONDITIONS (VDD = 3.3V \pm 0.3V, TA = 0 to 70 \pm)

Parameter	Value	Unit
Input levels (Vih/Vil)	2.4 / 0.4	V
Input timing measurement reference level	1.4	V
Input rise and fall time	tr / tf = 1 / 1	ns
Output timing measurement reference level	1.4	V
Output load condition	See Fig. 2	



(Fig. 1) DC Output Load Circuit



(Fig. 2) AC Output Load Circuit

OPERATING AC PARAMETER

(AC operating conditions unless otherwise noted)

Parameter	Symbol	Version			Unit	Note
		-8	-10	-12		
Row active to row active delay	trRD(min)	16	20	24	ns	1
RAS to CAS delay	trCD(min)	20	24	26	ns	1
Row precharge time	trP(min)	20	24	26	ns	1
Row active time	trAS(min)	48	50	60	ns	1
	trAS(max)	100			us	
Row cycle time	@Operation trC(min)	70	80	90	ns	1
	@Auto refresh trFC(min)	80	80	90	ns	1, 5
Last data in to new col. address delay	tCDL(min)	1			CLK	2
Last data in to row precharge	trDL(min)	1			CLK	2
Last data in to burst stop	tBDL(min)	1			CLK	2
Col. address to col. address delay	tCCD(min)	1			CLK	3
Number of valid output data	CAS latency=3	2			ea	4
	CAS latency=2	1				

- Note :
1. The minimum number of clock cycles is determined by dividing the minimum time required with clock cycle time and then rounding off to the next higher integer.
 2. Minimum delay is required to complete write.
 3. All parts allow every cycle column address change.
 4. In case of row precharge interrupt, auto precharge and read burst stop.
 5. A new command may be given trFC after self refresh exit.



REV. 4 Mar. '97

KM416S4020A

CMOS SDRAM

AC CHARACTERISTICS (AC operating conditions unless otherwise noted)

Parameter		Symbol	-8		-10		-12		Unit	Note
			Min	Max	Min	Max	Min	Max		
CLK cycle time	CAS latency=3	tcc	8	1000	10	1000	12	1000	ns	1
	CAS latency=2		12		13		15			
CLK to valid output delay	CAS latency=3	tsac		6		7		8	ns	1, 2
	CAS latency=2			6		7		8		
Output data hold time	CAS latency=3	toH	3		3		3		ns	2
	CAS latency=2		3		3		3			
CLK high pulse width		tch	3		3.5		4		ns	3
CLK low pulse width		tcl	3		3.5		4		ns	3
Input setup time		tss	2		2.5		3		ns	3
Input hold time		tsh	1		1		1		ns	3
CLK to output in Low-Z		tslz	1		1		1		ns	2
CLK to output in Hi-Z	CAS latency=3	tshz		6		7		8	ns	
	CAS latency=2			6		7		8		

- Note :
- Parameters depend on programmed CAS latency.
 - If clock rising time is longer than 1ns, $(tr/2-0.5)ns$ should be added to the parameter.
 - Assumed input rise and fall time $(tr \& \; tf)=1ns$.
If $tr \& \; tf$ is longer than 1ns, transient time compensation should be considered, i.e., $[(tr + tf)/2-1]ns$ should be added to the parameter.



REV. 4 Mar. '97

KM416S4020A**CMOS SDRAM****FREQUENCY vs. AC PARAMETER RELATIONSHIP TABLE****KM416S4020AT-8**

(Unit : number of clock)

Frequency	CAS Latency	trc	trAs	trP	trRD	trCD	tccD	tcdL	trDL
		70ns	48ns	20ns	16ns	20ns	8ns	8ns	8ns
125MHz (8.0ns)	3	9	6	3	2	3	1	1	1
100MHz (10.0ns)	3	7	5	2	2	2	1	1	1
83MHz (12.0ns)	2	6	4	2	2	2	1	1	1
75MHz (13.0ns)	2	6	4	2	2	2	1	1	1
66MHz (15.0ns)	2	5	4	2	2	2	1	1	1

KM416S4020AT-10

(Unit : number of clock)

Frequency	CAS Latency	trc	trAs	trP	trRD	trCD	tccD	tcdL	trDL
		80ns	50ns	24ns	20ns	24ns	10ns	10ns	10ns
100MHz (10.0ns)	3	8	5	3	2	3	1	1	1
83MHz (12.0ns)	3	7	5	2	2	2	1	1	1
75MHz (13.0ns)	2	6	4	2	2	2	1	1	1
66MHz (15.0ns)	2	6	4	2	2	2	1	1	1
60MHz (16.7ns)	2	5	3	2	2	2	1	1	1

KM416S4020AT-12

(Unit : number of clock)

Frequency	CAS Latency	trc	trAs	trP	trRD	trCD	tccD	tcdL	trDL
		90ns	60ns	26ns	24ns	26ns	12ns	12ns	12ns
83MHz (12.0ns)	3	8	5	3	2	3	1	1	1
75MHz (13.0ns)	3	7	5	2	2	2	1	1	1
66MHz (15.0ns)	2	6	4	2	2	2	1	1	1
60MHz (16.7ns)	2	6	4	2	2	2	1	1	1
50MHz (20.0ns)	2	5	3	2	2	2	1	1	1

SIMPLIFIED TRUTH TABLE

COMMAND		CKEn-1	CKEn	\overline{CS}	\overline{RAS}	\overline{CAS}	\overline{WE}	DQM	BA	A10/AP	A12 ~ A11, A9 ~ A0	Note	
Register	Mode Register Set	H	X	L	L	L	L	X	OP CODE			1, 2	
Refresh	Auto Refresh	H	H	L	L	L	H	X	X			3	
	Entry		L									3	
	Self Refresh	Exit	L	H	L	H	H	H	X	X			3
					H	X	X	X					3
Bank Active & Row Addr.		H	X	L	L	H	H	X	V	Row Address			
Read & Column Address	Auto Precharge Disable	H	X	L	H	L	H	X	V	L	Column Address (A0-A7)	4	
	Auto Precharge Enable									H		4, 5	
Write & Column Address	Auto Precharge Disable	H	X	L	H	L	L	X	V	L	Column Address (A0-A7)	4	
	Auto Precharge Enable									H		4, 5	
Burst Stop		H	X	L	H	H	L	X	X			6	
Precharge	Bank Selection	H	X	L	L	H	L	X	V	L	X		
	Both Banks								X	H			
Clock Suspend or Active Power Down	Entry	H	L	H	X	X	X	X	X				
	Exit			L	V	V	V						
Precharge Power Down Mode	Entry	H	L	H	X	X	X	X	X				
				L	H	H	H						
	Exit	L	H	H	X	X	X	X					
				L	V	V	V						
DQM		H	X					V	X		7		
No Operation Command		H	X	H	X	X	X	X	X				
L	H			H	H								

(V=Valid, X=Don't Care, H=Logic High, L=Logic Low)

Note : 1. OP Code : Operand Code

A0 ~ A12, BA : Program keys. (@MRS)

2. MRS can be issued only at both banks precharge state.

A new command can be issued after 2 CLK cycles of MRS.

3. Auto refresh functions are as same as CBR refresh of DRAM.

The automatical precharge without row precharge command is meant by "Auto".

Auto/self refresh can be issued only at both banks precharge state.

4. BA : Bank select address.

If "Low" at read, write, row active and precharge, bank A is selected.

If "High" at read, write, row active and precharge, bank B is selected.

If A10/AP is "High" at row precharge, BA is ignored and both banks are selected.

5. During burst read or write with auto precharge, new read/write command can not be issued.

Another bank read/write command can be issued after the end of burst.

New row active of the associated bank can be issued at trp after the end of burst.

6. Burst stop command is valid at every burst length.

7. DQM sampled at positive going edge of a CLK masks the data-in at the very CLK (Write DQM latency is 0), but makes Hi-Z state the data-out of 2 CLK cycles after. (Read DQM latency is 2)

